



SOT-23 Plastic-Encapsulate Transistors

S8550LT1 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.3 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

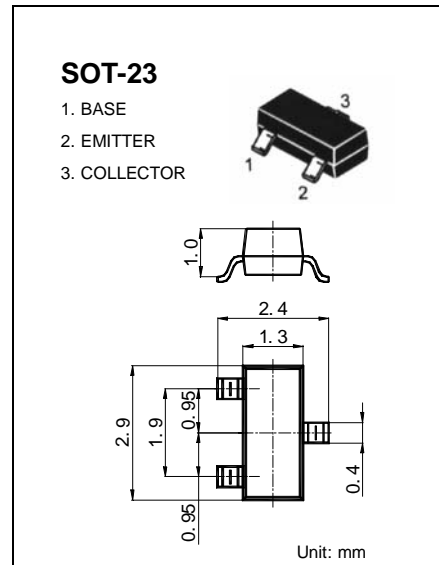
$$I_{CM}: -0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40\text{V}, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20\text{V}, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	120	350	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -500\text{mA}$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f = 30\text{MHz}$	150		MHz

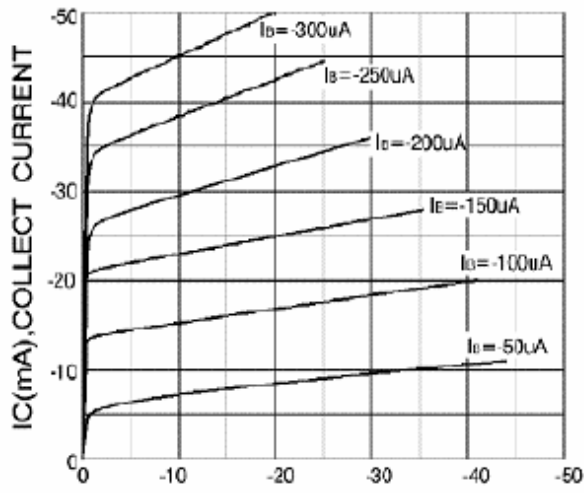
CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H
Range	120-200	200-350

DEVICE MARKING	S8550LT1=2TY
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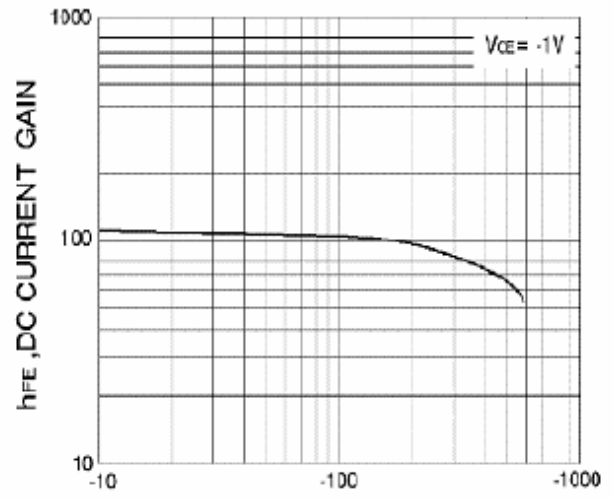
Typical Characteristics

S8550LT1



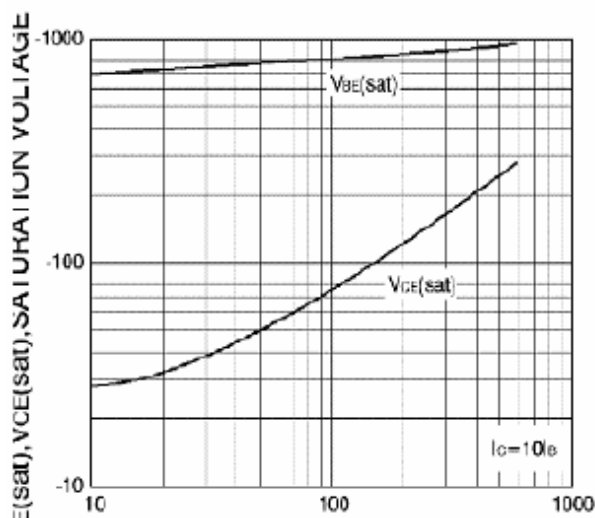
V_{CE} (V), COLLECTOR-EMITTER VOLTAGE

Static Characteristic



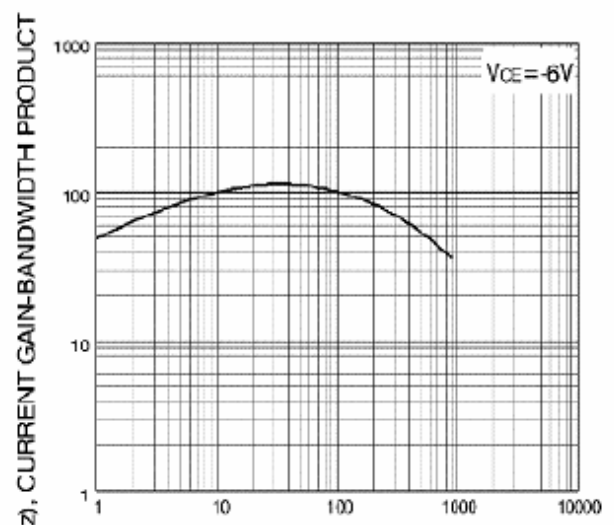
I_C (mA), COLLECTOR CURRENT

DC current Gain



I_C (mA), COLLECTOR CURRENT

Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage



I_C (mA), COLLECTOR CURRENT

Current Gain Bandwidth Product